

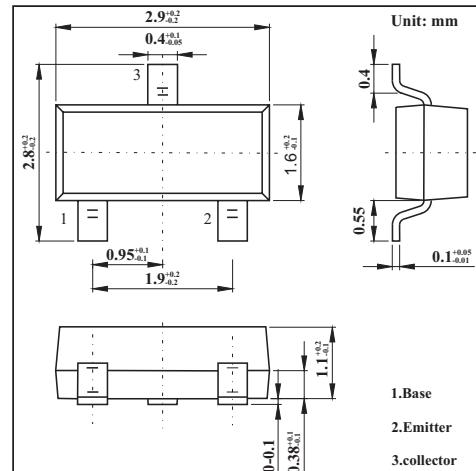
SOT-23-3 Plastic-Encapsulate Transistors

FEATURES

- Large I_c. ICMax=-500mA
- Low V_{ce(sat)}. Ideal for low -voltage operation
- PNP TRANSISTORS

MECHANICAL DATA

- Case style:SOT-23-3 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-40	V
Collector-emitter voltage	V _{CEO}	-32	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current *	I _C	-0.5	A
Collector power dissipation	P _C	0.2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* P_C max must not be exceeded

Parameter	Symbol	Test Conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C = -100 μA	-40			V
Collector-emitter breakdown voltage	V _{CEO}	I _C = -1 mA	-32			V
Emitter-base breakdown voltage	V _{EBO}	I _E = -100 μA	-5			V
Collector cutoff current	I _{CBO}	V _{CB} = -20 V			-1	μ A
Emitter cutoff current	I _{EBO}	V _{EB} = -4 V			-1	μ A
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _C = -10mA			-0.4	V
DC current gain	h _{FE}	V _{CE} = -3V, I _C = -10mA	82		390	
Output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0A, f = 1MHz		7		pF
Transition frequency	f _T	V _{CE} = -5V, I _E = 20mA, f = 100MHz		200		MHz

RATINGS AND CHARACTERISTIC CURVES

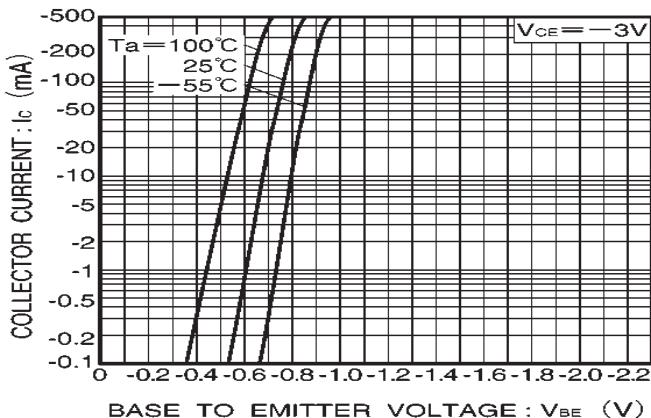


Fig.1 Grounded emitter propagation

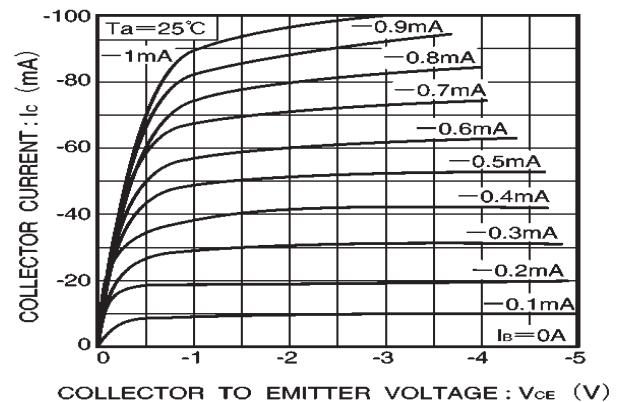


Fig.2 Grounded emitter output characteristics (I)

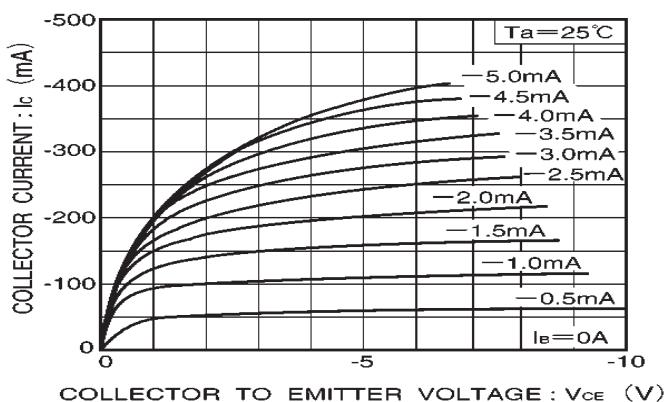


Fig.3 Grounded emitter output characteristics (II)

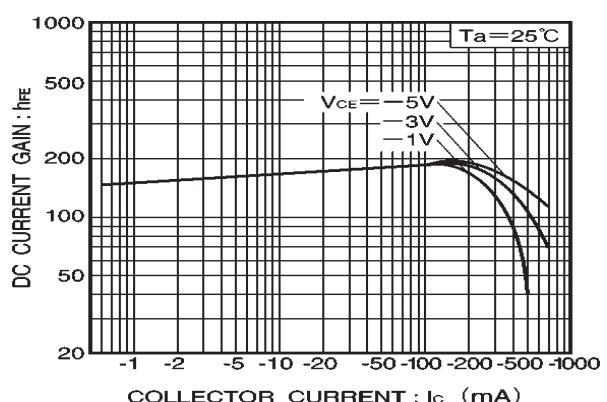


Fig.4 DC current gain vs. collector current (I)

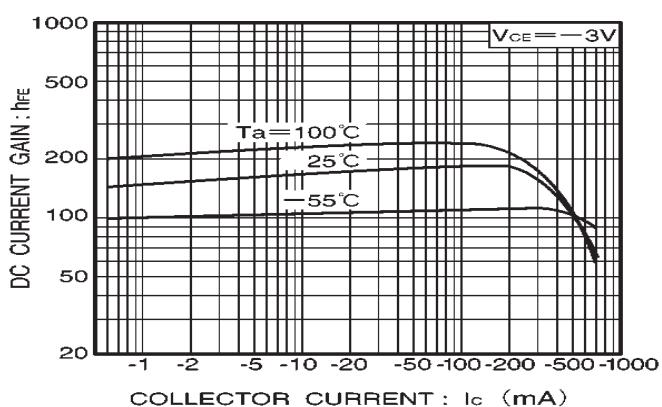


Fig.5 DC current gain vs. collector current (II)

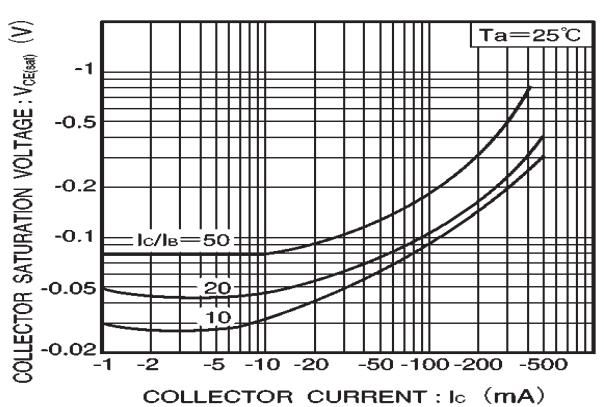


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

RATINGS AND CHARACTERISTIC CURVES

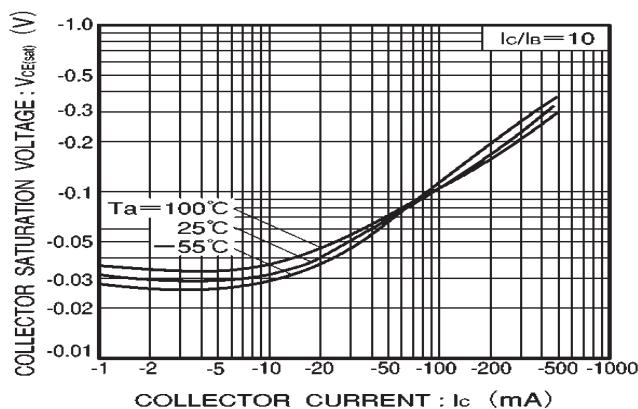


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

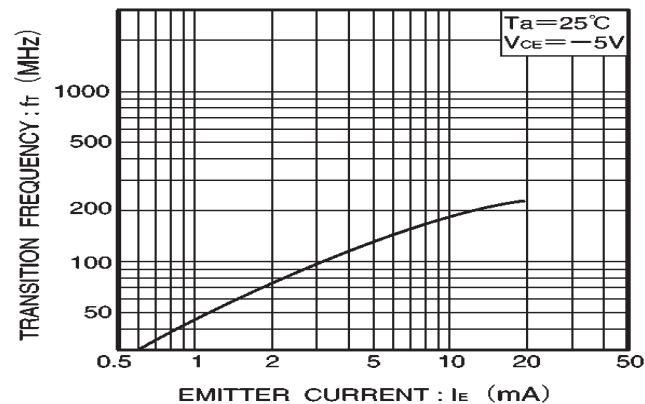


Fig.8 Gain bandwidth product vs. emitter current

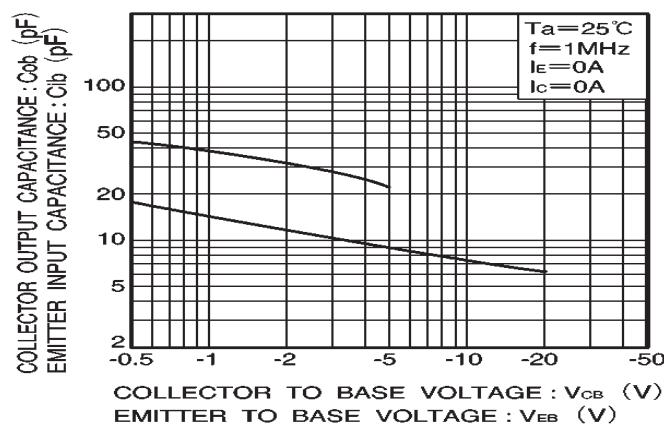


Fig.9 Collector output capacitance vs. collector-base voltage. Emitter input capacitance vs. emitter-base voltage